

Taiwan Semiconductor

N-Channel Power MOSFET

30V, 73A, 8mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive Losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

PRODUCT SUMMARY				
PARAMETER		VALUE	UNIT	
V_{DS}		30	V	
D ()	$V_{GS} = 10V$	8	0	
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	12.5	mΩ	
Q_g		7.2	nC	

Pb





APPLICATIONS

- DC-DC Converters
- Battery Power Management
- ORing FET/Load Switch

PDFN56



Notes: MSL 1 (Moisture Sensitivity Level) per J-STD-020

	Pin 5 , 6 , 7 , 8 Drain	
Pin 4 Gate O	*	

Source Pin 1, 2, 3

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	l _D	73	Δ	
Continuous Drain Current	$T_A = 25^{\circ}C$		14	А	
Pulsed Drain Current (Note 1)		I _{DM}	292	Α	
Single Pulse Avalanche Current (Note 2)		I_{AS}	23	Α	
Single Pulse Avalanche Energy (Note 2)		E _{AS}	26	mJ	
Total Power Dissipation	$T_C = 25^{\circ}C$	D	69	W	
Total Fower Dissipation	$T_C = 125$ °C	P_{D}	14		
Total Dawer Dissipation	$T_A = 25$ °C	Б	2.6	W	
Total Power Dissipation	$T_A = 125^{\circ}C$	P _D	0.5	VV	
Operating Junction and Storage Temperature Range		T_J,T_STG	- 55 to +150	°C	

THERMAL RESISTANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Thermal Resistance – Junction to Case	R _{OJC}	1.8	°C/W	
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	48	°C/W	

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

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ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	I _{GSS}			±100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 30V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 14A$			6.5	8	mΩ
(Note 3)	$V_{GS} = 4.5V, I_D = 14A$	R _{DS(on)}		9.5	12.5	
Forward Transconductance (Note 3)	$V_{DS} = 5V, I_{D} = 14A$	g _{fs}		30		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 14A$	Q_g		14.4		
Total Gate Charge	45)/	Q_g		7.2		nC
Gate-Source Charge	$V_{GS} = 4.5V, V_{DS} = 15V,$	Q_gs		2.6		
Gate-Drain Charge	I _D = 14A	Q_gd		3.3		
Input Capacitance		C _{iss}		843		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$	C _{oss}		157		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		95		
Gate Resistance	f = 1.0MHz, open drain	R_g	0.9	3	6	Ω
Switching (Note 4)						
Turn-On Delay Time		t _{d(on)}		4.8		
Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 14A, R_{G} = 3.3\Omega$	t _r		12.5		
Turn-Off Delay Time		t _{d(off)}		27.6		ns
Fall Time		t _f		8.2		
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 15A$	V _{SD}			1	V
Reverse Recovery Time	I _S = 14A,	t _{rr}		16		ns
Reverse Recovery Charge	di/dt = 100A/µs	Q _{rr}		8.3		nC

Notes:

- 1. Current limited by package.
- 2. $L=0.1mH,\ V_{GS}=10V,\ V_{DS}=25V,\ R_G=25\Omega,\ I_{AS}=23A,\ Starting\ T_J=25^{\circ}C$
- 3. Pulse test: Pulse Width \leq 300 μ s, duty cycle \leq 2%.
- 4. Switching time is essentially independent of operating temperature.

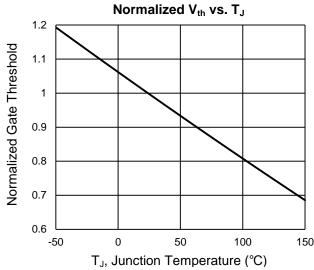
ORDERING INFORMATION

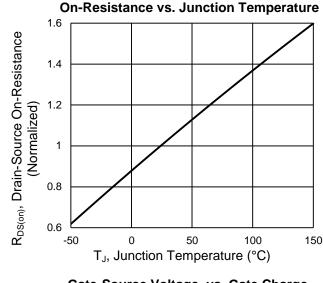
PART NO.	PACKAGE	PACKING
TSM080N03PQ56 RLG	PDFN56	2,500pcs / 13" Reel

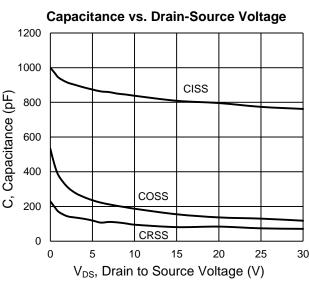


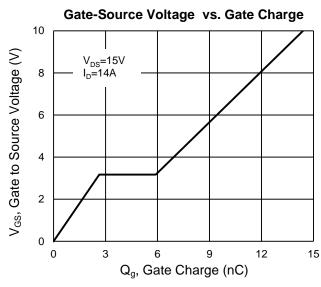
CHARACTERISTICS CURVES

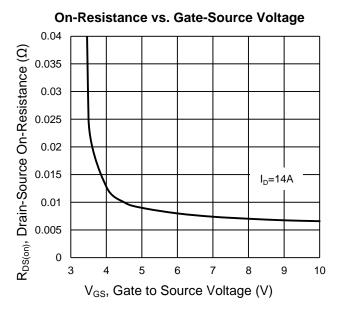
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

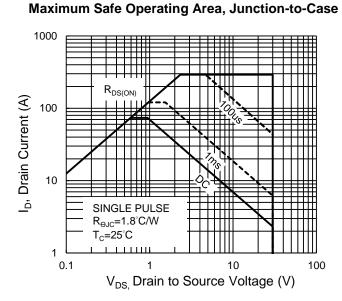












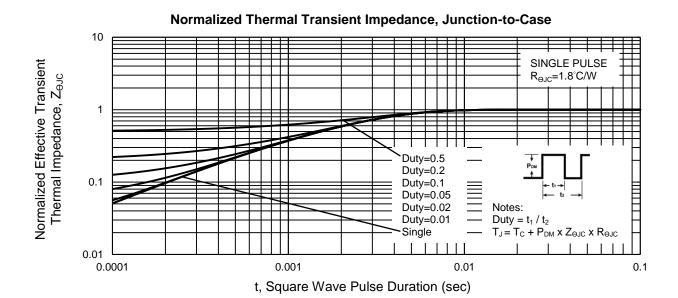
Version: D1608

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CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)



Version: D1608

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0.51 ±0.1

 3.58 ± 0.2

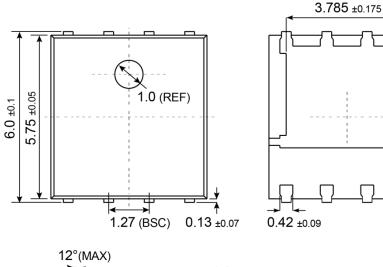
(NIM)

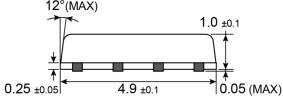
 0.61 ± 0.1



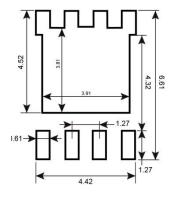
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

PDFN56





SUGGESTED PAD LAYOUT (Unit: Millimeters)



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MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

 \mathbf{W} =Sep \mathbf{X} =Oct \mathbf{Y} =Nov \mathbf{Z} \mathbf{L} = Lot Code (1~9, A~Z)



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